



### September 1996

# NDT452P

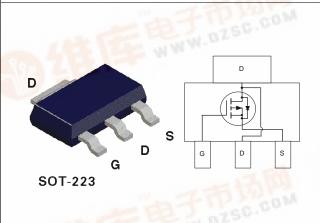
# P-Channel Enhancement Mode Field Effect Transistor

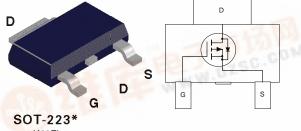
## **General Description**

Power SOT P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and DC motor control.

#### Features

- -3A, -30V.  $R_{DS(ON)} = 0.18\Omega @ V_{GS} = -10V.$
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability in a widely used surface mount package.



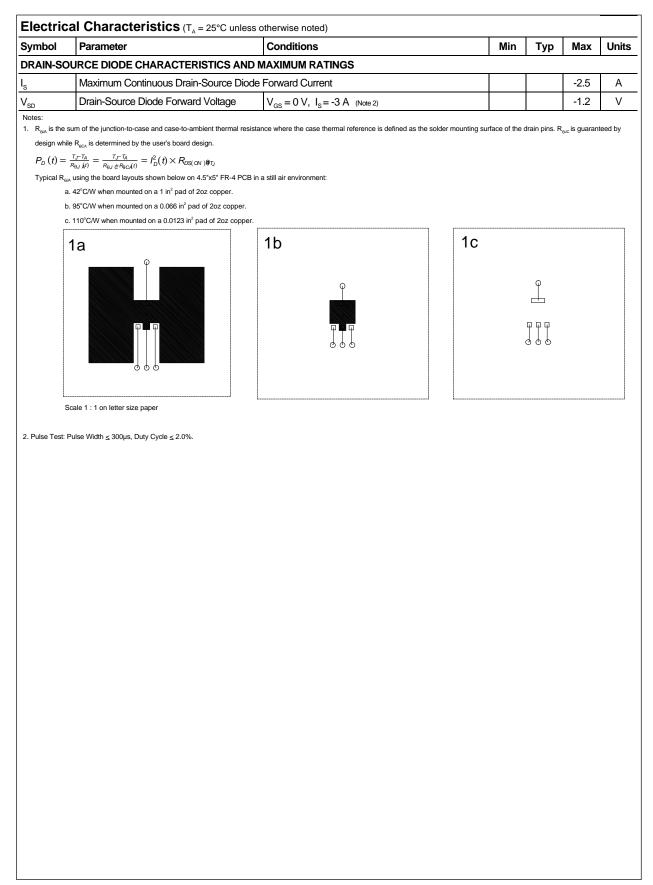


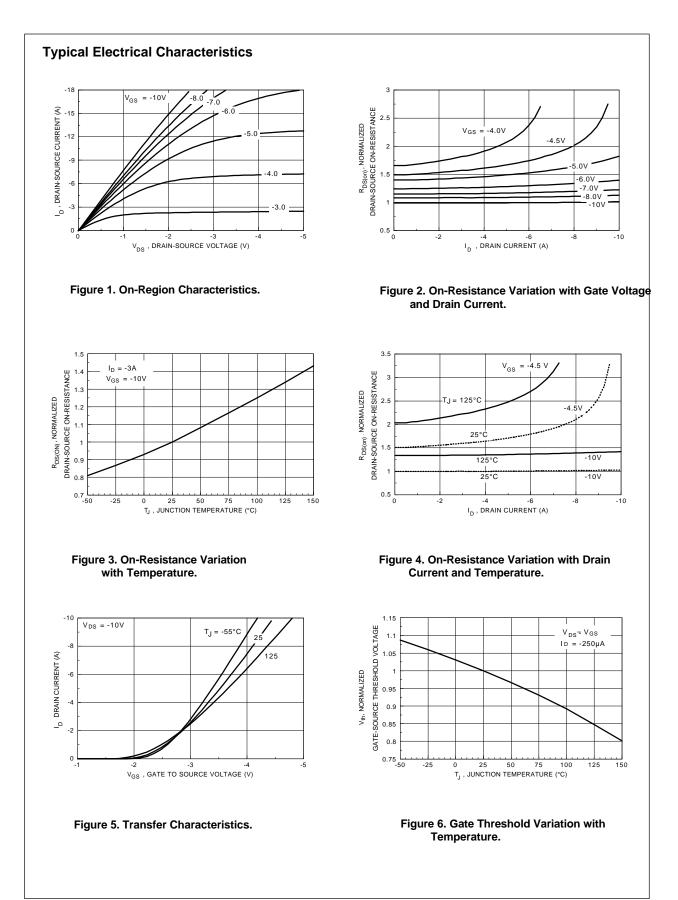
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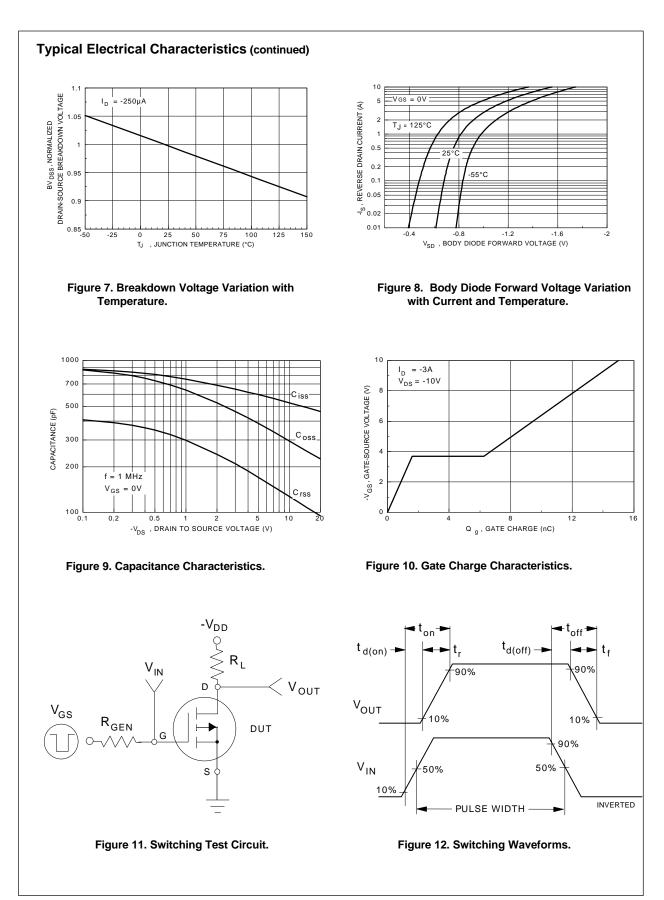
Symbol	Parameter		NDT452P	Units
V <sub>DSS</sub>	Drain-Source Voltage		-30	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
D	Drain Current - Continuous	(Note 1a)	±3	А
	- Pulsed		±20	
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	3	W
		(Note 1b)	1.3	
	WW.025	(Note 1c)	1.1	
T <sub>J</sub> ,T <sub>STG</sub>	Operating and Storage Temperature Range		-65 to 150	°C
THERM/	AL CHARACTERISTICS			
R <sub>ØJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	42	
۲ <sub>өлс</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	12	°C/W

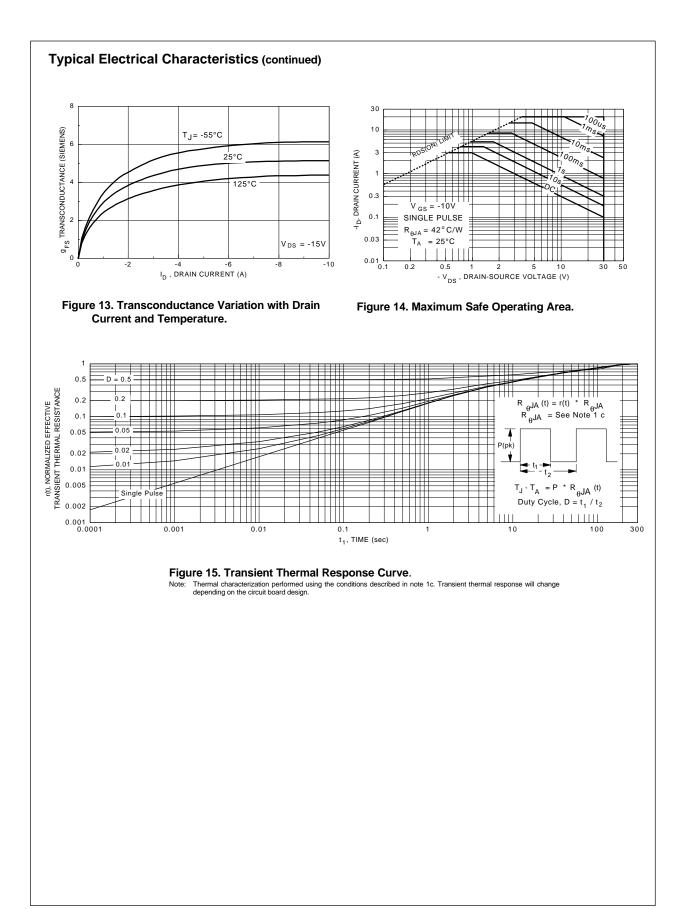
# 1997 Fairchild Semiconductor Corporation

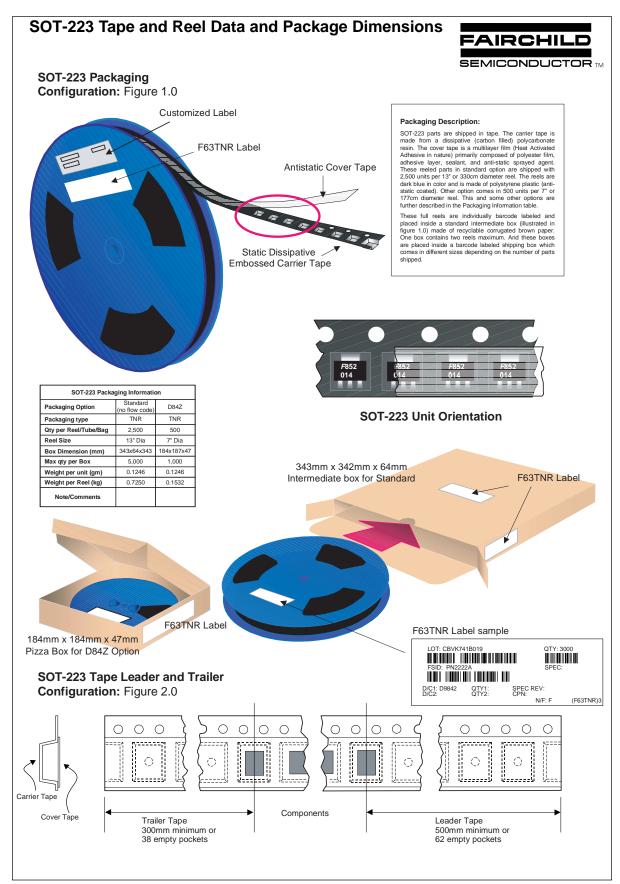
Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHA	RACTERISTICS	·					·
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$		-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -24 V, V_{GS} = 0 V$				-2	μA
			$T_{J} = 55^{\circ}C$			-25	μA
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				100	nA
I <sub>GSSR</sub>	Gate - Body Leakage, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V				-100	nA
ON CHAR	ACTERISTICS (Note 2)						
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{\rm DS}=V_{\rm GS},\ I_{\rm D}=-250\ \mu A$		-1	-2	-3	V
			T <sub>J</sub> =125°C	-0.85	-1.7	-2.6	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_{D} = -3 \text{ A}$			0.15	0.18	Ω
			T <sub>J</sub> =125°C		0.23	0.32	
		$V_{GS} = -4.5 \text{ V}, \ \text{I}_{D} = -2.2 \text{ A}$			0.27	0.32	
I <sub>D(on)</sub>	On-State Drain Current $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$			-15			А
		$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$		-4.5			
g <sub>fs</sub>	Forward Transconductance	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -3 \text{ A}$			3.7		S
DYNAMIC	CHARACTERISTICS					1	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			525		pF
C <sub>oss</sub>	Output Capacitance				300		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				130		pF
SWITCHIN	IG CHARACTERISTICS (Note 2)					1	
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{\text{DD}} = -10 \text{ V}, \text{ I}_{\text{D}} = -1.0 \text{ A},$ $V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$			8	40	ns
ţ	Turn - On Rise Time				15	40	ns
t <sub>D(off)</sub>	Turn - Off Delay Time				25	90	ns
t,	Turn - Off Fall Time				8	50	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = -10 V,$ $I_{D} = -3 A, V_{GS} = -10 V$			15	25	nC
Q <sub>gs</sub>	Gate-Source Charge				1.6	4	nC
$Q_{gd}$	Gate-Drain Charge				4.5	8	nC

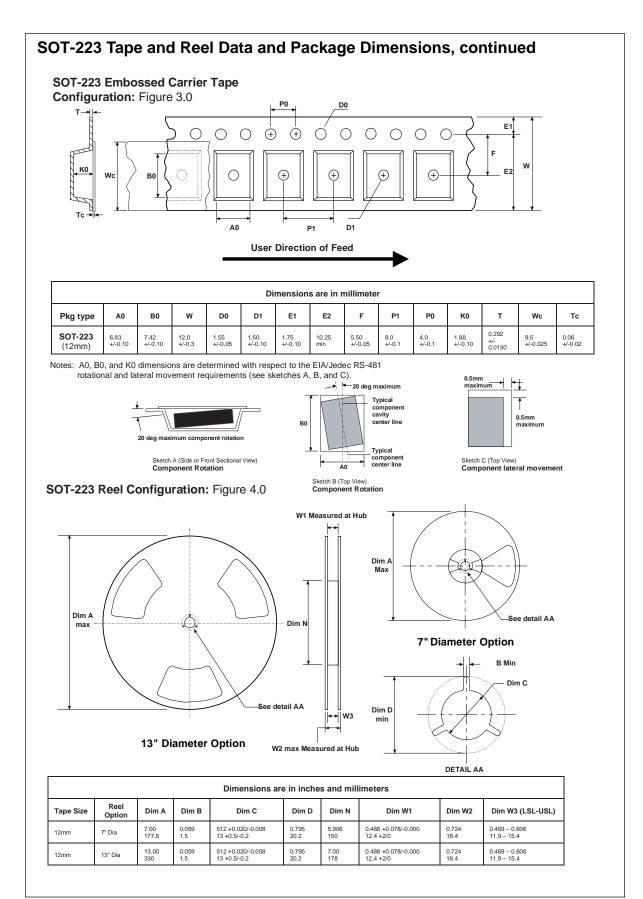


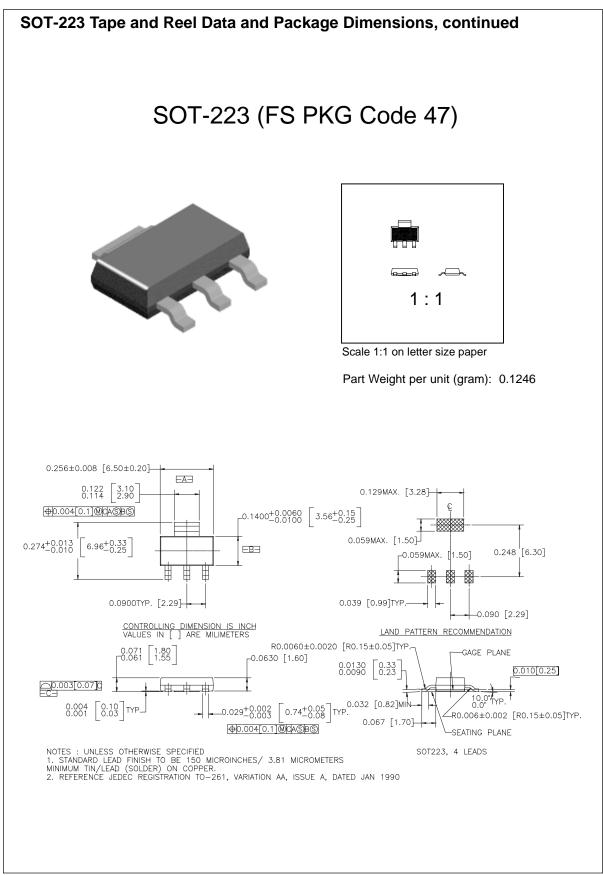












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